

65,536 x 8 HIGH-SPEED CMOS EPROM

NOVEMBER 1997

FEATURES

- · Fast access time: 45 ns
- Pin compatible with the IS27C512
- · Low power consumption
 - 50 μA CMOS standby
- Industrial and commercial temperature ranges available
- High-speed write programming
 - Typically less than eight seconds
- 5 ±10% power supply tolerance available
- JEDEC-approved pinout
- Standard 28-pin DIP, and TSOP, and 32-pin PLCC packages

DESCRIPTION

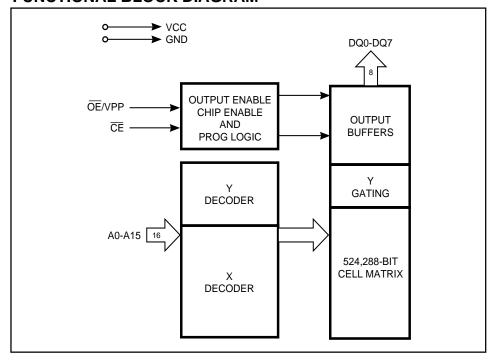
The *ISSI* IS27HC512 is an ultra-high-speed 512K-bit CMOS Programmable Read-Only Memory. It utilizes the standard JEDEC pinout making it functionally compatible with the IS27C512, but with significantly fast access capability. This superior random access capability results from a focused high-speed design. This offers users bipolar speeds with higher density, lower cost and proven reliability.

The device is ideal for use with the faster processors. This IS27HC512 completely eliminates performance-draining wait states without using bank-interleaving and caching techniques. Designers may take full advantage of high-speed digital signal processors and microprocessors by allowing code to be executed at full speed directly out of EPROM. Typical applications include laser printers, switching networks, graphics, workstations, high-speed modems, and digital signal processing.

The IS27HC512 uses ISSI's write programming algorithm which allows the entire chip to be programmed in typically less than thirty seconds.

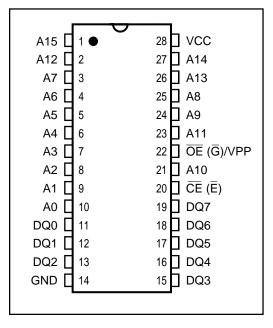
This product is available in One-Time Programmable (OTP) PDIP, PLCC, and TSOP packages over commercial and industrial temperature ranges.

FUNCTIONAL BLOCK DIAGRAM



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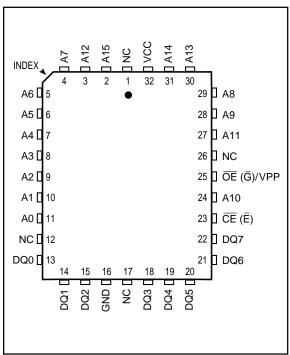
PIN CONFIGURATIONS 28-Pin DIP



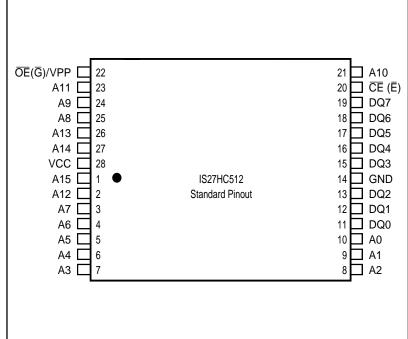
PIN DESCRIPTIONS

A0-A15	Address Inputs
CE (E)	Chip Enable Input
DQ0-DQ7	Data Inputs/Outputs
OE (G)/VPP	Output Enable Input/ Program Voltage Input
Vcc	Power Supply Voltage
GND	Ground
NC	No Internal Connection

32-Pin PLCC



28-Pin TSOP



FUNCTIONAL DESCRIPTION

Programming the IS27HC512

Upon delivery, the IS27HC512 has 524,288 bits in the "ONE", or HIGH state. "ZEROs" are loaded into the IS27HC512 through the procedure of programming.

The programming mode is entered when $12.5 \pm 0.25 \text{V}$ is applied to the $\overline{\text{OE}}/\text{VPP}$ pin, Vcc = 6 V and $\overline{\text{CE}}$ is at VlL. For programming, the data to be programmed is applied eight bits in parallel to the data output pins.

The write programming algorithm reduces programming time by using 100 μs programming pulses followed by a byte verification to determine whether the byte has been successfully programmed. If the data does not verify, an additional pulse is applied for a maximum of 25 pulses. This process is repeated while sequencing through each address of the EPROM.

The write programming algorithm programs and verifies at Vcc = 6V and $\overline{OE}/Vpp = 12.5V$. After the final address is completed, all byte are compared to the original data with Vcc = 5.25V.

Program Inhibit

Programming of multiple IS27HC512s in parallel with different data is also easily accomplished. Except for \overline{CE} , all like inputs of the parallel IS27HC512 may be common. A TTL low-level program pulse applied to an IS27HC512 \overline{CE} input with $\overline{OE}/V_{PP}=12.5\pm0.25V$ will program that IS27HC512. A high-level \overline{CE} input inhibits the other IS27HC512 from being programmed.

Program Verify

A verify should be performed on the programmed bits to determine that they were correctly programmed. The verify should be performed with $\overline{\text{CE}}$ at V_{IL} and $\overline{\text{OE}}/\text{V}_{\text{PP}}$ at V_{IL} .

Auto Select Mode

The auto select mode allows the reading out of a binary code from an EPROM that will identify its manufacturer and type. This mode is intended for use by programming equipment for the purpose of automatically matching the device to be programmed with its corresponding programming algorithm. This mode is functional in the 25°C \pm 5°C ambient temperature range that is required when programming the IS27HC512.

To activate this mode, the programming equipment must force $12.0 \pm 0.5 \text{V}$ on address line A9 of the IS27HC512. Two identifier bytes may then be sequenced from the device outputs by toggling address line A0 from V_{IL} to V_{IH}. All other address lines must be held at V_{IL} during auto select mode.

Byte 0 (A0 = V_{IL}) represents the manufacturer code, and byte 1 (A0 = V_{IH}), the device identifier code. For the IS27HC512, these two identifier bytes are given in the Mode Select table. All identifiers manufacturer and device codes will possess odd parity, with the MSB (DQ7) defined as the parity bit.

Read Mode

The IS27HC512 has two control functions, both of which must be logically satisfied in order to obtain data at the outputs. Chip Enable (\overline{CE}) is the power control and should be used for device selection. Assuming that addresses are stable, address access time (tacc) is equal to the delay from \overline{CE} to output (tce). Output Enable (\overline{OE}) is the output control and should be used to get data to the output pins, independent of device selection. Data is available at the outputs toe after the falling edge of \overline{OE} assuming that \overline{CE} has been LOW and addresses have been stable for at least tacc – toe.

Standby Mode

The IS27HC512 has a standby mode which reduces the maximum Vcc active current. It is placed in standby mode when $\overline{\text{CE}}$ is at Vih. The amount of current drawn in standby mode depends on the frequency and the number of address pins switching. The IS27HC512 is specified with 50% of the address lines toggling at 5 MHz. A reduction of the frequency or quantity of address lines toggling will significantly reduce the actual standby current.

Output OR-Tieing

To accommodate multiple memory connections, a twoline control function is provided to allow for:

- 1. Low memory power dissipation, and
- Assurance that output bus contention will not occur.

It is recommended that $\overline{\text{CE}}$ be decoded and used as the primary device-selecting function, while $\overline{\text{OE}}/\text{VPP}$ be made a common connection to all devices in the array and connected to the READ line from the system control bus. This assures that all deselected memory devices are in their low-power standby mode and that the output pins are only active when data is desired from a particular memory device.

System Applications

During the switch between active and standby conditions, transient current peaks are produced on the rising and falling edges of Chip Enable. The magnitude of these transient current peaks is dependent on the output capacitance loading of the device at a minimum, a 0.1 μF ceramic capacitor (high-frequency, low inherent inductance) should be used on each device between Vcc and GND to minimize transient effects. In addition, to overcome the voltage drop caused by the inductive effects of the printed circuit board traces on EPROM arrays, a 4.7 μF bulk electrolytic capacitor should be used between Vcc and GND for each eight devices. The location of the capacitor should be close to where the power supply is connected to the array.

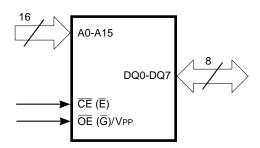
TRUTH TABLE(1,2,4)

Mode		CE	OE/ Vpp	A0	A9	Outputs
Read		VIL	VIL	Х	Х	D оит
Output Disable		Х	ViH	Х	Х	Hi-Z
Standby		ViH	Х	Х	Х	Hi-Z
Program		VIL	VPP	Х	Х	Din
Program Verify		VIL	VIL	Х	Х	D оит
Program Inhibit		ViH	VPP	Х	Х	Hi-Z
Auto Select ^(3,5)	Manufacturer Code	VIL	VIL	VIL	Vн	D5H
	Device Code	V_{IL}	VIL	Vih	Vн	91H

Notes:

- 1. $V_H = 12.0V \pm 0.5V$.
- 2. X = Either VIH or VIL.
- 3. A1-A8 = A10-A15 = VIL
- 4. See DC Programming Characteristics for VPP voltage during programming.
- 5. The IS27HC512 can use the same write algorithm during program as other IS27C512 or IS27512 devices.

LOGIC SYMBOL



ABSOLUTE MAXIMUM RATINGS(1)

Symbol	Parameter	Value	Unit
VTERM	Terminal Voltage with Respect to GND		
	All pins except A9 and VPP	-0.6 to Vcc + $0.5^{(2)}$	V
	VPP	$Vcc - 0.3$ to $13.5^{(2,3)}$	V
	A9	-0.6 to 13.5 ^(2,3)	V
	Vcc	-0.6 to 7.0 ⁽²⁾	V
TA	Ambient Temperature with Power Applied	-65 to +125	°C
Tstg	Storage Temperature (OTP)	-65 to +125	°C
Тѕтс	Storage Temperature (All others)	-65 to +150	°C

Notes:

- Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the
 device. This is a stress rating only and functional operation of the device at these or any other conditions above
 those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum
 rating conditions for extended periods may affect reliability.
- 2. Minimum DC input voltage is -0.5V. During transitions, inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 3. Maximum DC voltage on A9 or VPP may overshoot to +13.5V for periods less than 10 ns.

OPERATING RANGE

Range	Ambient Temperature	Vcc
Commercial	0°C to +70°C	5V ± 10%
Industrial ⁽¹⁾	–40°C to +85°C	5V ± 10%

Note:

1. Operating ranges define those limits between which the functionally of the device is guaranteed.

DC ELECTRICAL CHARACTERISTICS(1,2,3) (Over Operating Range)

Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage	Vcc = Min., IoH = -4.0 mA	2.4	_	V
Vol	Output LOW Voltage	Vcc = Min., IoL = 8.0 mA	_	0.45	V
ViH	Input HIGH Voltage(4)		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage(4)		-0.3	0.8	V
Li	Input Load Current	VIN = 0V to +Vcc	_	5.0	μΑ
ILO	Output Leakage Current	Vout = 0V to +Vcc	_	10	μΑ

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27HC512 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.
- 4. Tested under static DC conditions.

POWER SUPPLY CHARACTERISTICS(1,2,4) (Over Operating Range)

Symbol	Parameter	Test Conditions		Min.	Max.	Unit
Icc1	Vcc Operating Supply Current ⁽³⁾	$Vcc = Max., \overline{CE} = V_{IL}$ Comme Iout = 0 mA, f = 5 MHz Indus (Open outputs)		_	15 20	mA
Iccsb0	Vcc CMOS Standby Current	$\overline{\text{CE}} \ge \text{Vcc} - 0.3\text{V}$ All pins $\ge \text{Vcc} - 0.3\text{V}$ or $\le 0.3\text{V}$		_	50	μΑ
ICCSB1	Vcc TTL Standby Current	CE ≥ VIH All pins = VIH or VIL (TTL level)		_	1	mA

Notes:

- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP. Never try to force VPP LOW to 1V below Vcc. Manufacturer suggests to tie VPP and Vcc together during the READ operation.
- 2. Caution: the IS27HC512 must not be removed from (or inserted into) a socket when Vcc or VPP is applied.
- 3. Icc1 is tested with $\overline{OE}/VPP = VIH$ to simulate open outputs.
- 4. Minimum DC input voltage is -0.5V. During transitions, the inputs may undershoot to -2.0V for periods less than 10 ns. Maximum DC voltage on output pins is Vcc + 0.5V which may overshoot to Vcc + 2.0V for periods less than 10 ns.

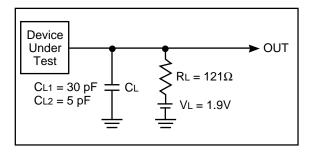
CAPACITANCE(1,2,3)

			D	IP	PLC	C/TSOP	
Symbol	Parameter	Conditions	Тур.	Max.	Тур.	Max.	Unit
Cin	Input Capacitance	VIN = 0V	6	10	6	9	pF
Соит	Output Capacitance	Vout = 0V	8	12	6	9	pF
CIN \overline{OE}/V_{PP}	OE/Vpp Capacitance	OE/Vpp = 0V	12	15	12	15	pF

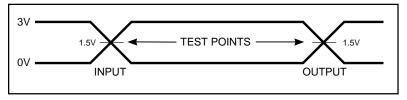
Notes:

- 1. Typical values are for nominal supply voltage.
- 2. This parameter is only sampled, but not 100% tested.
- 3. Test conditions: $T_A = 25^{\circ}C$, f = 1 MHz.

SWITCHING TEST CIRCUIT



SWITCHING TEST WAVEFORM



Notes:

AC Testing:

- 1. Inputs are driven at 3.0V for a logic "1" and 0V for a logic "0".
- 2. Input pulse rise and fall times are \geq 1.5V/ns.

SWITCHING CHARACTERISTICS(1,2,3,4) (Over Operating Range)

JEDEC	Std.			-4	15	-:	55	-7	70	
Symbol	Symbol	Parameter	Test Conditions	Min.	Max.	Min.	Max.	Min.	Max.	Unit
t avqa	tacc	Address to Output Delay	$\overline{CE} = \overline{OE} = V_{IL}$ $C_L = C_L 1$	_	45	_	55	_	70	ns
t ELQV	tce	Chip Enable to Output Delay	OE = VIL CL = CL1	_	45	_	55	_	70	ns
tGLQV	toe	Output Enable to Output Delay	CE = VIL CL = CL1	_	20	_	25	_	35	ns
teнoz, tgнqz	t DF ⁽²⁾	Chip Enable HIGH or Output Enable HIGH, whichever comes first, to Output Float	CL = CL2	0	20	0	25	0	30	ns
tavox	tон	Output Hold from Address, CE or OE whichever occured first		0	_	0	_	0	_	ns

Notes:

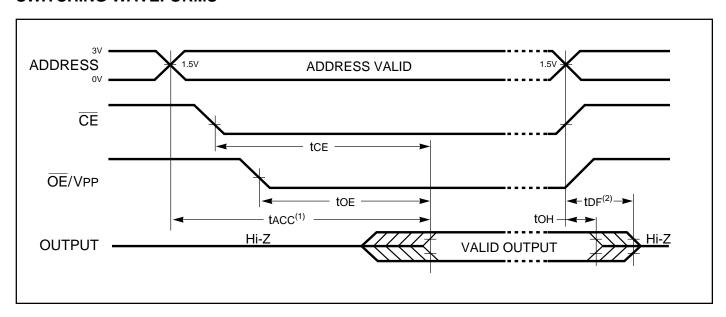
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- 2. This parameter is only sampled, not 100% tested.
- 3. Caution: The IS27HC512 must not be removed from (or inserted into) a socket or board when VPP or Vcc applied.
- 4. Output Load: 1 TTL gate and C = CL.

Input Rise and Fall times: 2 ns.

Input Pulse Levels: 0 to 3V.

Timing Measurement Reference Level: 1.5V for inputs and outputs.

SWITCHING WAVEFORMS



- 1. \overline{OE} may be delayed \underline{up} to \underline{tacc} toe after the falling edge of \overline{CE} without impact on tacc. 2. \underline{tof} is specified from \overline{OE} or \overline{CE} , whichever occurs first.

DC PROGRAMMING CHARACTERISTICS(1,2,3) (TA = +25°C ± 5 °C)

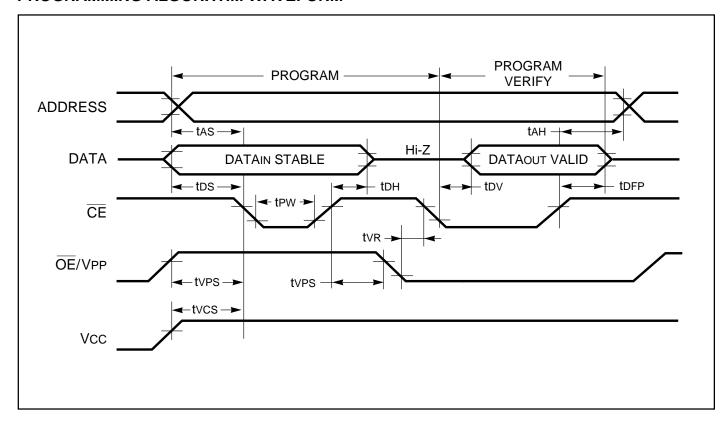
Symbol	Parameter	Test Conditions	Min.	Max.	Unit
Vон	Output HIGH Voltage During Verify	Іон = –400 μА	2.4	_	V
Vol	Output LOW Voltage During Verify	IoL = 2.1 mA	_	0.45	V
ViH	Input HIGH Voltage		2.0	Vcc + 0.5	V
VIL	Input LOW Voltage (All Inputs)		-0.3	0.8	V
Vн	A9 Auto Select Voltage		11.5	12.5	V
ILI	Input Current (All Inputs)	VIN = VIL or VIH	_	10.0	μΑ
Icc	Vcc Supply Current (Program & Verify)		_	50	mA
I PP	VPP Supply Current	CE = VIL, OE = VIH	_	30	mA
Vcc	Supply Voltage		5.75	6.25	V
VPP	Programming Voltage		12.25	12.75	V

SWITCH PROGRAMMING CHARACTERISTICS (1,2,3) (TA = +25°C \pm 5°C)

JEDEC Symbol	Std. Symbol	Parameter	Min.	Max.	Unit
tavel	tas	Address Setup Time	2	_	μs
t EHGL	t oeh	OE/VPP Hold Time	2	_	μs
tovel	tos	Data Setup Time	2	_	μs
t GHAX	t AH	Address Hold Time	0	_	μs
t EHDX	t DH	Data Hold Time	2	_	μs
t EHQZ	t DFP	CE HIGH to Output Float Delay	0	130	ns
tvps	tvps	VPP Setup Time	2	_	μs
teleh1	t PW	CE Program Pulse Width	95	105	μs
tvcs	tvcs	Vcc Setup Time	2	_	μs
t GLEL	t vr	OE/VPP Recovery Time	2	_	μs
t ELQV	t dv	Data Valid from CE	_	150	ns

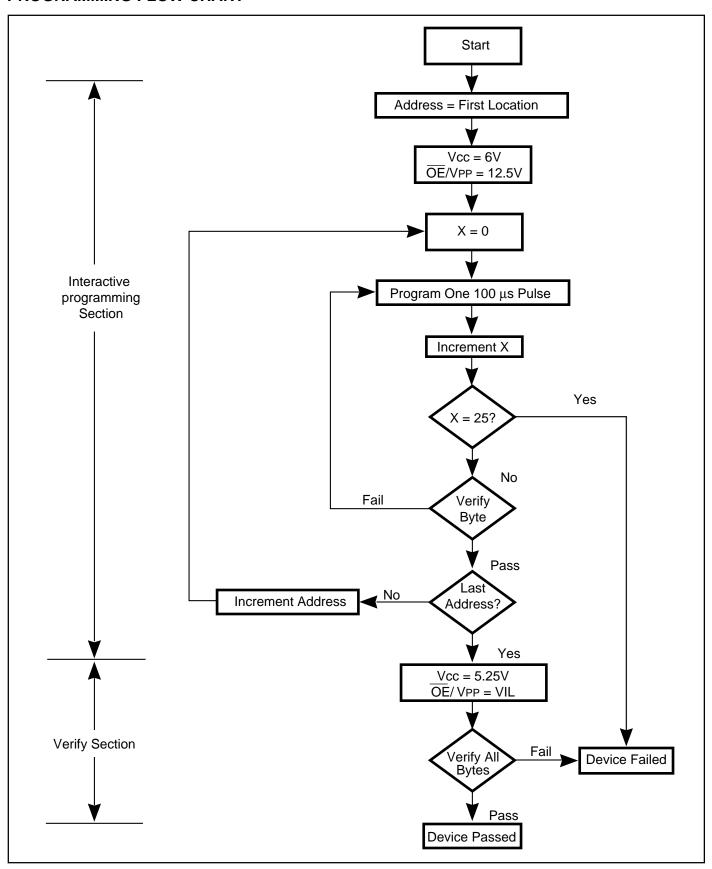
- 1. Vcc must be applied simultaneously or before VPP and removed simultaneously or after VPP.
- 2. When programming IS27LV512, a 0.1 μF capacitor is required across V_{PP} and ground to suppress spurious voltage transients which may damage the device.
- 3. Programming characteristics are sampled but not 100% tested at worst-case conditions.

PROGRAMMING ALGORITHM WAVEFORM(1,2)



- The timing reference level is 0.8V to 2V for inputs and outputs.
 toe and tdep are characteristics of the device but must be accommodated by the programmer.

PROGRAMMING FLOW CHART



ORDERING INFORMATION

Commercial Range: 0°C to +70°C

Speed (ns)	Order Part Number	Package
45	IS27HC512-45W IS27HC512-45PL IS27HC512-45T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
55	IS27HC512-55W IS27HC512-55PL IS27HC512-55T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP
70	IS27HC512-70W IS27HC512-70PL IS27HC512-70T	600-mil Plastic DIP PLCC – Plastic Leaded Chip Carrier TSOP

ORDERING INFORMATION

Industrial Range: -40°C to +85°C

Speed (ns)	Order Part Number	Package
45	IS27HC512-45PLI IS27HC512-45TI	PLCC – Plastic Leaded Chip Carrier TSOP
55	IS27HC512-55PLI IS27HC512-55TI	PLCC – Plastic Leaded Chip Carrier TSOP
70	IS27HC512-70PLI IS27HC512-70TI	PLCC – Plastic Leaded Chip Carrier TSOP



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